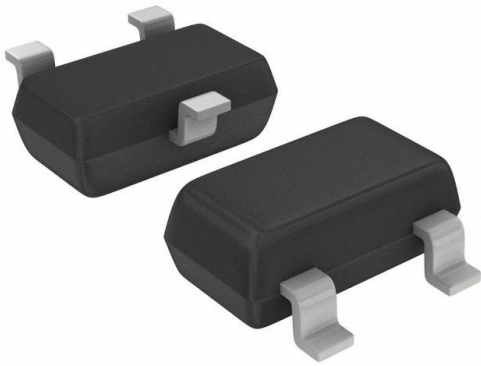


MUN2236T1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

| | |
|------------------------------|---|
| DiGi Electronics Part Number | MUN2236T1G-DG |
| Manufacturer | onsemi |
| Manufacturer Product Number | MUN2236T1G |
| Description | TRANS PREBIAS NPN 50V 0.1A SC59 |
| Detailed Description | Pre-Biased Bipolar Transistor (BJT) NPN - Pre-Biased 50 V 100 mA 338 mW Surface Mount SC-59 |



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

MUN2236T1G

Series:

-

Transistor Type:

NPN - Pre-Biased

Voltage - Collector Emitter Breakdown (Max):

50 V

Resistor - Emitter Base (R2):

100 kOhms

Vce Saturation (Max) @ Ib, Ic:

250mV @ 300μA, 10mA

Power - Max:

338 mW

Package / Case:

TO-236-3, SC-59, SOT-23-3

Base Product Number:

MUN2236

Manufacturer:

onsemi

Product Status:

Last Time Buy

Current - Collector (Ic) (Max):

100 mA

Resistor - Base (R1):

100 kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

80 @ 5mA, 10V

Current - Collector Cutoff (Max):

500nA

Mounting Type:

Surface Mount

Supplier Device Package:

SC-59

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

Digital Transistors (BRT)

R1 = 100 kΩ, R2 = 100 kΩ

NPN Transistors with Monolithic Bias Resistor Network

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

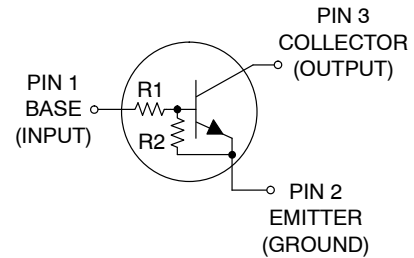
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

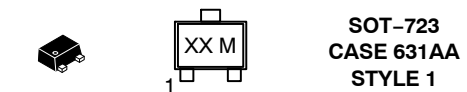
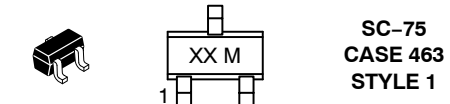
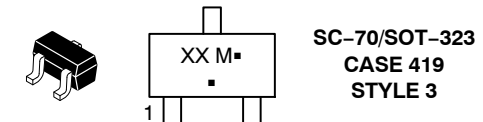
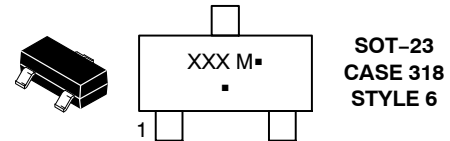
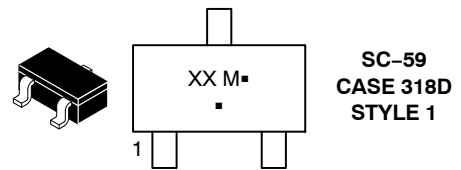
| Rating | Symbol | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage | V _{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current - Continuous | I _C | 100 | mAdc |
| Input Forward Voltage | V _{IN(fwd)} | 40 | Vdc |
| Input Reverse Voltage | V _{IN(rev)} | 10 | Vdc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code
 M = Date Code*
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3**Table 1. ORDERING INFORMATION**

| Device | Part Marking | Package | Shipping† |
|--------------------------------|--------------|----------------------------|--------------------|
| NSVMUN2236T1G* | 8N | SC-59 (Pb-Free) | 3000 / Tape & Reel |
| MMUN2236LT1G, NSVMMUN2236LT1G* | AA5 | SOT-23 (Pb-Free) | 3000 / Tape & Reel |
| MUN5236T1G, NSVMUN5236T1G* | 8N | SC-70/SOT-323 (Pb-Free) | 3000 / Tape & Reel |
| DTC115EET1G | 8N | SC-75 (Pb-Free) | 3000 / Tape & Reel |
| DTC115EM3T5G | 8N | SOT-723 (Pb-Free) | 8000 / Tape & Reel |

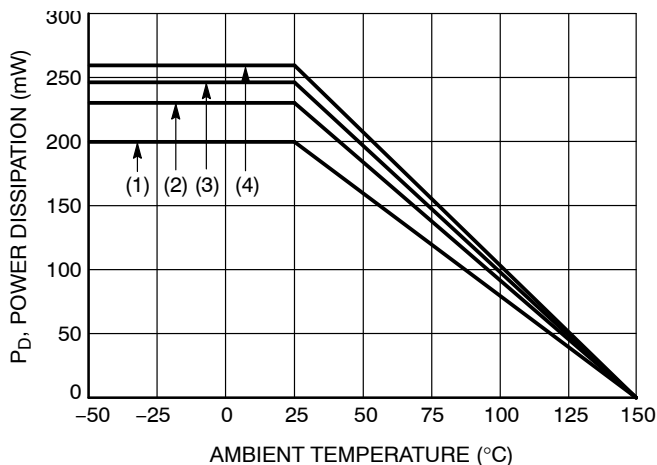
DISCONTINUED (Note 1)

| | | | |
|------------|----|--------------------|--------------------|
| MUN2236T1G | 8N | SC-59 (Pb-Free) | 3000 / Tape & Reel |
|------------|----|--------------------|--------------------|

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3**Table 2. THERMAL CHARACTERISTICS**

| Characteristic | | Symbol | Max | Unit |
|--|----------|-----------------|-------------|-------|
| THERMAL CHARACTERISTICS (SC-59) (MUN2236) | | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ | (Note 2) | P_D | 230 | mW |
| Derate above 25°C | (Note 3) | | 338 | mW/°C |
| | (Note 2) | | 1.8 | |
| | (Note 3) | | 2.7 | |
| Thermal Resistance, Junction to Ambient | (Note 2) | $R_{\theta JA}$ | 540 | °C/W |
| | (Note 3) | | 370 | |
| Thermal Resistance, Junction to Lead | (Note 2) | $R_{\theta JL}$ | 264 | °C/W |
| | (Note 3) | | 287 | |
| Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SOT-23) (MMUN2236L) | | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ | (Note 2) | P_D | 246 | mW |
| Derate above 25°C | (Note 3) | | 400 | mW/°C |
| | (Note 2) | | 2.0 | |
| | (Note 3) | | 3.2 | |
| Thermal Resistance, Junction to Ambient | (Note 1) | $R_{\theta JA}$ | 508 | °C/W |
| | (Note 3) | | 311 | |
| Thermal Resistance, Junction to Lead | (Note 2) | $R_{\theta JL}$ | 174 | °C/W |
| | (Note 3) | | 208 | |
| Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5236) | | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ | (Note 2) | P_D | 202 | mW |
| Derate above 25°C | (Note 3) | | 310 | mW/°C |
| | (Note 2) | | 1.6 | |
| | (Note 3) | | 2.5 | |
| Thermal Resistance, Junction to Ambient | (Note 2) | $R_{\theta JA}$ | 618 | °C/W |
| | (Note 3) | | 403 | |
| Thermal Resistance, Junction to Lead | (Note 2) | $R_{\theta JL}$ | 280 | °C/W |
| | (Note 3) | | 332 | |
| Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SC-75) (DTC115EE) | | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ | (Note 2) | P_D | 200 | mW |
| Derate above 25°C | (Note 3) | | 300 | mW/°C |
| | (Note 2) | | 1.6 | |
| | (Note 3) | | 2.4 | |
| Thermal Resistance, Junction to Ambient | (Note 2) | $R_{\theta JA}$ | 600 | °C/W |
| | (Note 3) | | 400 | |
| Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SOT-723) (DTC115EM3) | | | | |
| Total Device Dissipation $T_A = 25^\circ\text{C}$ | (Note 2) | P_D | 260 | mW |
| Derate above 25°C | (Note 3) | | 600 | mW/°C |
| | (Note 2) | | 2.0 | |
| | (Note 3) | | 4.8 | |
| Thermal Resistance, Junction to Ambient | (Note 2) | $R_{\theta JA}$ | 480 | °C/W |
| | (Note 3) | | 205 | |
| Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +150 | °C |

2. FR-4 @ Minimum Pad.

3. FR-4 @ 1.0 x 1.0 Inch Pad.

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3**Table 3. ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$, unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|---------------|-----|-----|------|------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$) | I_{CBO} | – | – | 100 | nAdc |
| Collector–Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$) | I_{CEO} | – | – | 500 | nAdc |
| Emitter–Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$) | I_{EBO} | – | – | 0.05 | mAdc |
| Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | 50 | – | – | Vdc |
| Collector–Emitter Breakdown Voltage (Note 4) ($I_C = 2.0\text{ mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | 50 | – | – | Vdc |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (Note 4) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$) | h_{FE} | 80 | 150 | – | |
| Collector–Emitter Saturation Voltage (Note 4) ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$) | $V_{CE(sat)}$ | – | – | 0.25 | Vdc |
| Input Voltage (off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\ \mu\text{A}$) | $V_{i(off)}$ | – | 1.2 | 0.5 | Vdc |
| Input Voltage (on) ($V_{CE} = 0.3\text{ V}$, $I_C = 1.0\text{ mA}$) | $V_{i(on)}$ | 3.0 | 1.7 | – | Vdc |
| Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 5.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OL} | – | – | 0.2 | Vdc |
| Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.25\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OH} | 4.9 | – | – | Vdc |
| Input Resistor | R_1 | 70 | 100 | 130 | $\text{k}\Omega$ |
| Resistor Ratio | R_1/R_2 | 0.8 | 1.0 | 1.2 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

TYPICAL CHARACTERISTICS

MUN2236, MMUN2236L, MUN5236, NSVMUN5236, DTC115EE, DTC115EM3

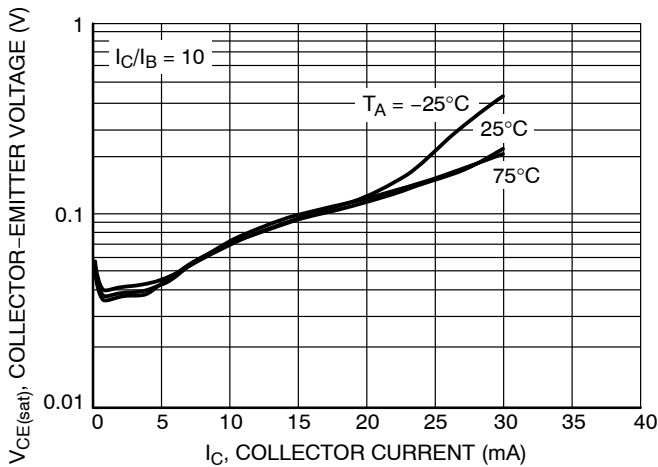


Figure 2. $V_{CE(sat)}$ versus I_C

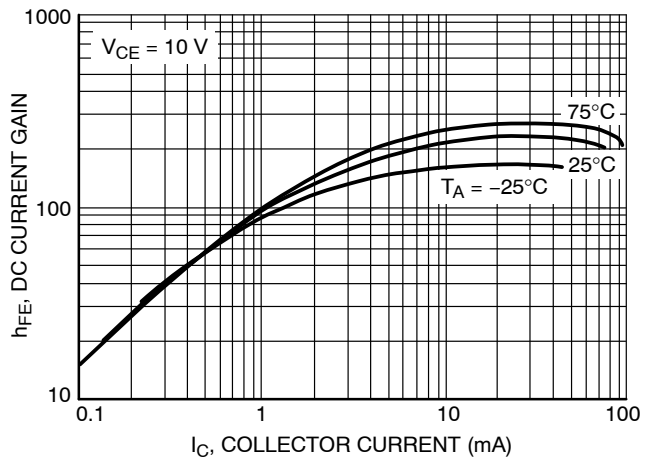


Figure 3. DC Current Gain

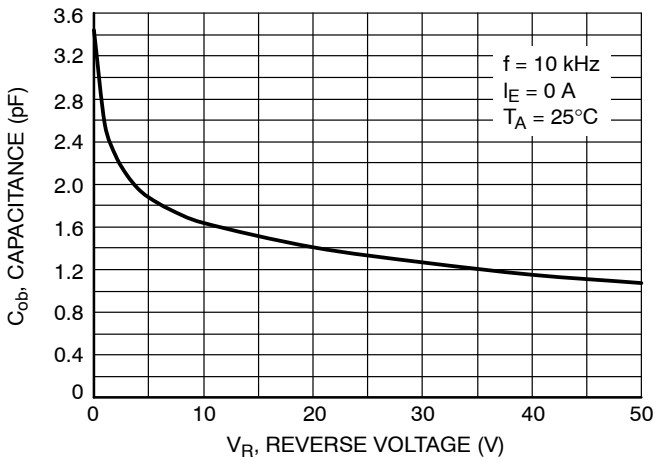


Figure 4. Output Capacitance

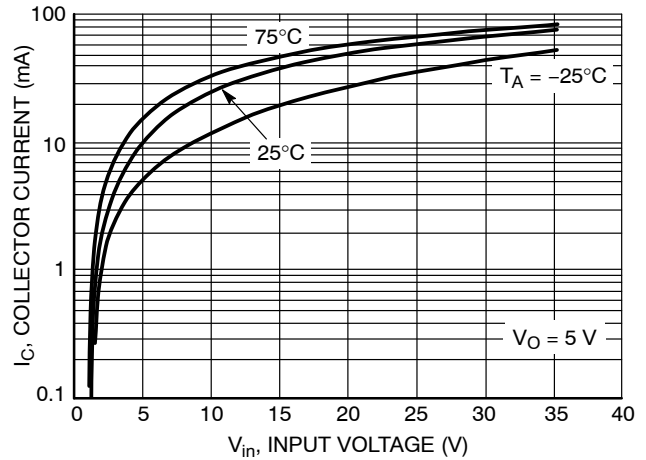


Figure 5. Output Current versus Input Voltage

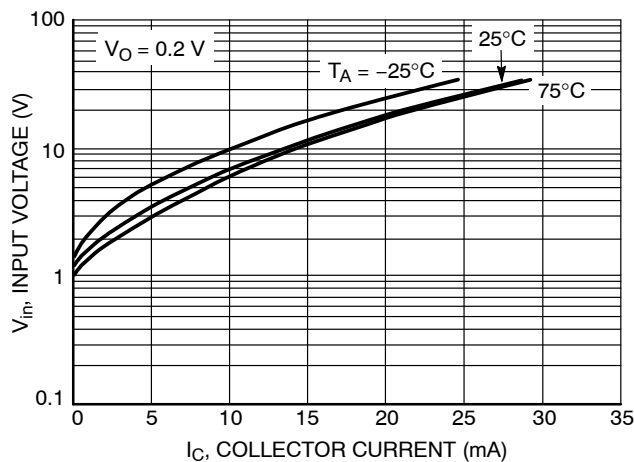
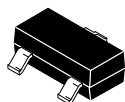


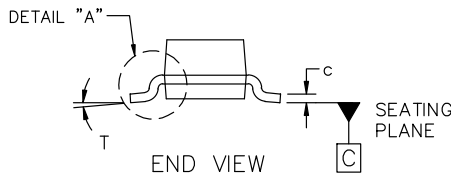
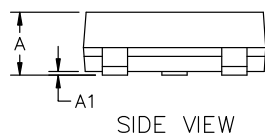
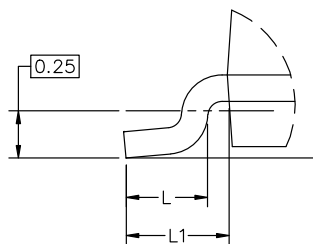
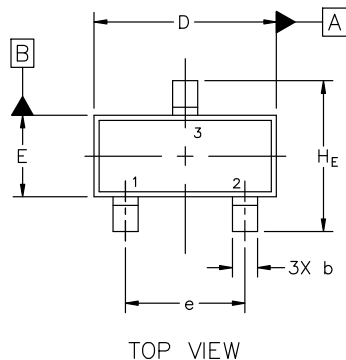
Figure 6. Input Voltage versus Output Current



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

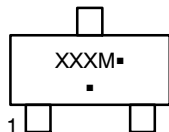
DATE 14 AUG 2024



| MILLIMETERS | | | |
|-------------|------|------|------|
| DIM | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 |
| A1 | 0.01 | 0.06 | 0.10 |
| b | 0.37 | 0.44 | 0.50 |
| c | 0.08 | 0.14 | 0.20 |
| D | 2.80 | 2.90 | 3.04 |
| E | 1.20 | 1.30 | 1.40 |
| e | 1.78 | 1.90 | 2.04 |
| L | 0.30 | 0.43 | 0.55 |
| L1 | 0.35 | 0.54 | 0.69 |
| HE | 2.10 | 2.40 | 2.64 |
| T | 0° | --- | 10° |

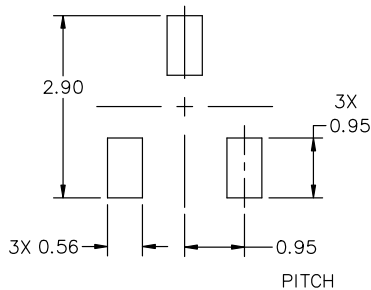
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
 2. CONTROLLING DIMENSIONS: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

| | | |
|-------------------------|---|--|
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| DESCRIPTION: | SOT-23 (TO-236) 2.90x1.30x1.00 1.90P | PAGE 1 OF 2 |

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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

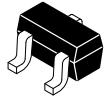
STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

| | | |
|-------------------------|---|---|
| DOCUMENT NUMBER: | 98ASB42226B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION: | SOT-23 (TO-236) 2.90x1.30x1.00 1.90P | PAGE 2 OF 2 |

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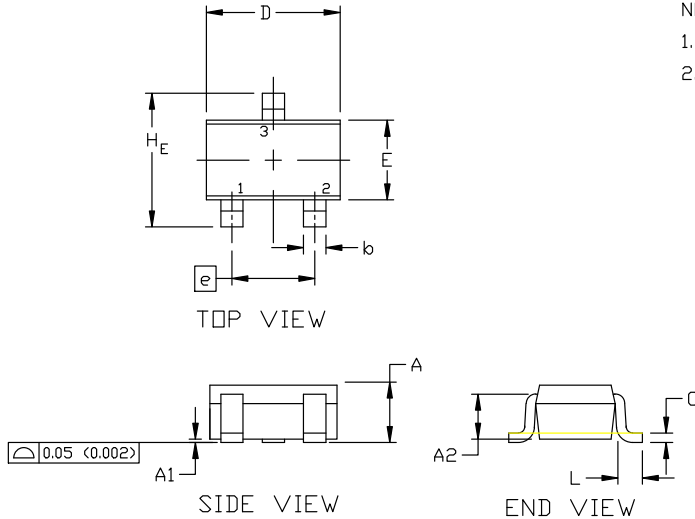
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



SCALE 4:1

**SC-70 (SOT-323)
CASE 419
ISSUE R**

DATE 11 OCT 2022

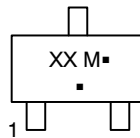


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

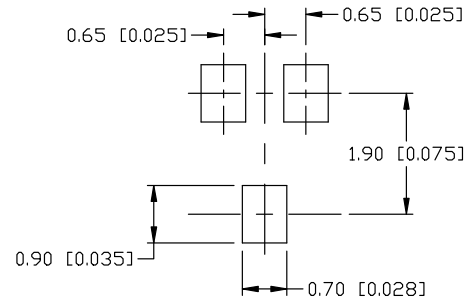
| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|-----------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| A2 | 0.70 REF | | | 0.028 BSC | | |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |
| c | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 |
| D | 1.80 | 2.00 | 2.20 | 0.071 | 0.080 | 0.087 |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e1 | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 |
| H _E | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 |

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1: CANCELLED | STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE | STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE | |
| STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE | STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE |

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|-------------------------|------------------------|---|
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| DESCRIPTION: | SC-70 (SOT-323) | PAGE 1 OF 1 |

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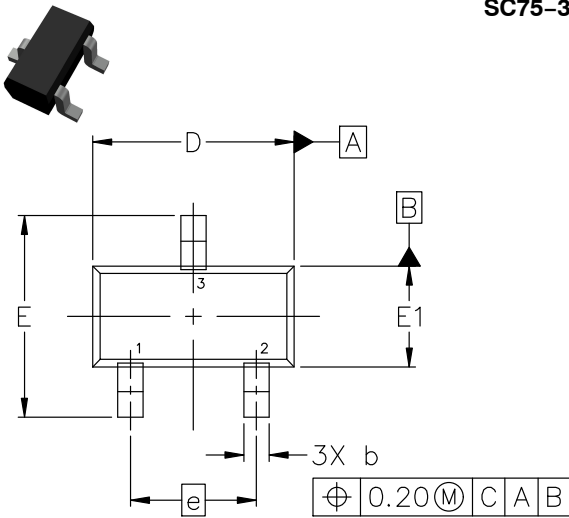
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

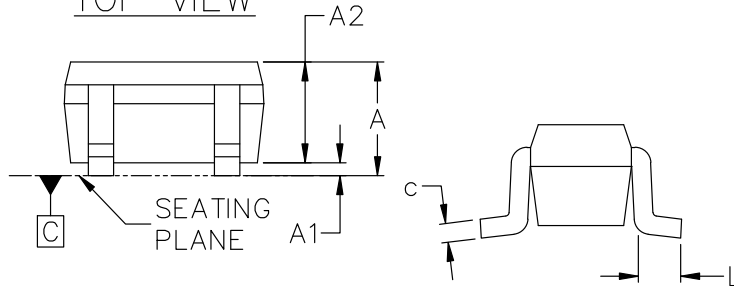
DATE 01 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.



TOP VIEW

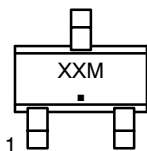


SIDE VIEW

END VIEW

| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.70 | 0.80 | 0.90 |
| A1 | 0.00 | 0.05 | 0.10 |
| A2 | 0.80 REF. | | |
| b | 0.15 | 0.20 | 0.30 |
| c | 0.10 | 0.15 | 0.25 |
| D | 1.55 | 1.60 | 1.65 |
| E | 1.50 | 1.60 | 1.70 |
| E1 | 0.70 | 0.80 | 0.90 |
| e | 1.00 BSC | | |
| L | 0.10 | 0.15 | 0.20 |

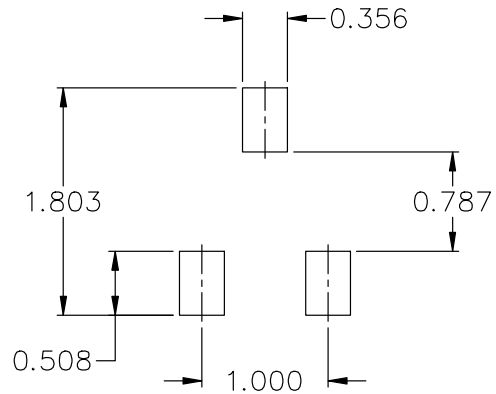
GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
- STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE
- STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
- STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN



RECOMMENDED MOUNTING FOOTPRINT*

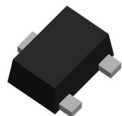
* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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| DESCRIPTION: | SC75-3 1.60x0.80x0.80, 1.00P | PAGE 1 OF 1 |

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**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



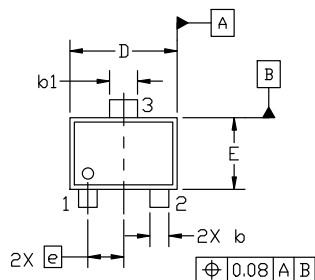
**SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E**

DATE 24 JAN 2024

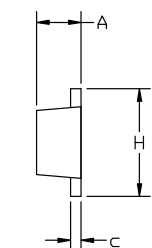
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

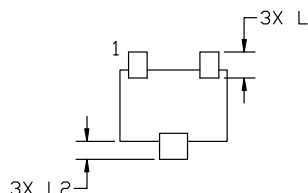
| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.45 | 0.50 | 0.55 |
| b | 0.15 | 0.21 | 0.27 |
| b1 | 0.25 | 0.31 | 0.37 |
| c | 0.07 | 0.12 | 0.17 |
| D | 1.15 | 1.20 | 1.25 |
| E | 0.75 | 0.80 | 0.85 |
| e | 0.40 BSC | | |
| H | 1.15 | 1.20 | 1.25 |
| L | 0.29 REF | | |
| L2 | 0.15 | 0.20 | 0.25 |



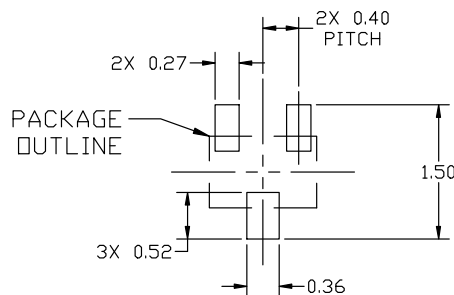
TOP VIEW



SIDE VIEW

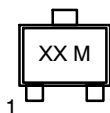


BOTTOM VIEW



RECOMMENDED MOUNTING FOOTPRINT

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | | | |
|---|--|--|--|--|
| STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE | STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN |
|---|--|--|--|--|

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| DESCRIPTION: | SOT-723 1.20x0.80x0.50, 0.40P | PAGE 1 OF 1 |

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